

TOSHIBA Field Effect Transistor Silicon P Channel MOS Type (U-MOSVI)

TPC8125

Lithium Ion Battery Applications
Power Management Switch Applications

- Small footprint due to small and thin package
- Low drain-source ON-resistance: $R_{DS(ON)} = 10 \text{ m}\Omega$ (typ.)
- Low leakage current: $I_{DSS} = -10 \mu\text{A}$ (max) ($V_{DS} = -30 \text{ V}$)
- Enhancement mode: $V_{th} = -0.8$ to -2.0 V ($V_{DS} = -10 \text{ V}$, $I_D = -0.5 \text{ mA}$)

Absolute Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit
Drain-source voltage		V_{DSS}	-30	V
Drain-gate voltage ($R_{GS} = 20 \text{ k}\Omega$)		V_{DGR}	-30	V
Gate-source voltage		V_{GSS}	-25/+20	V
Drain current	DC (Note 1)	I_D	-10	A
	Pulse (Note 1)	I_{DP}	-40	
Drain power dissipation (t = 10 s) (Note 2a)		P_D	1.9	W
Drain power dissipation (t = 10 s) (Note 2b)		P_D	1.0	W
Single pulse avalanche energy (Note 3)		E_{AS}	65	mJ
Avalanche current (Note 1)		I_{AR}	-10	A
Channel temperature		T_{ch}	150	°C
Storage temperature range		T_{stg}	-55 to 150	°C

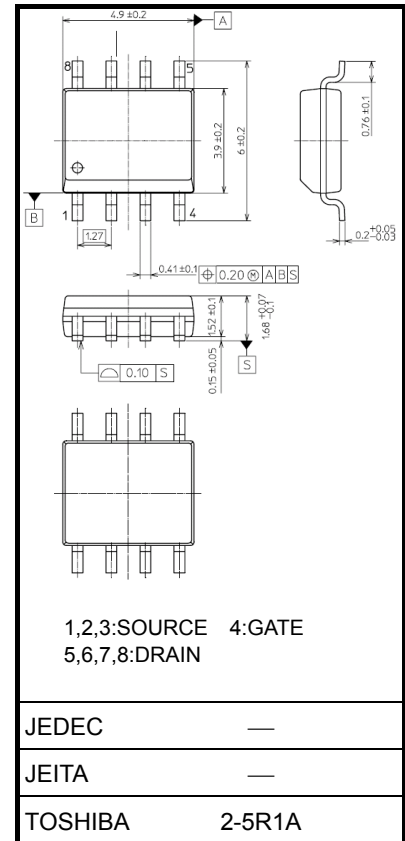
Note 1, Note 2, Note 3 : See the next page.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

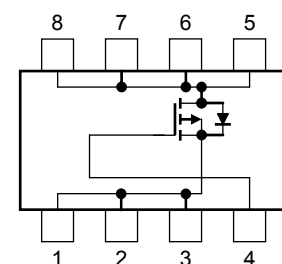
This transistor is an electrostatic-sensitive device. Handle with care.

Unit: mm



Weight: 0.085 g (typ.)

Circuit Configuration

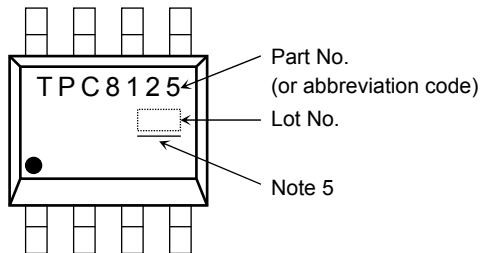


Start of commercial production
2009-11

Thermal Characteristics

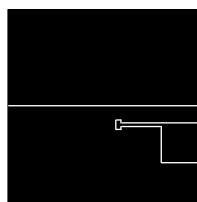
Characteristics	Symbol	Max	Unit
Thermal resistance, channel to ambient (t = 10 s) (Note 2a)	$R_{th} (ch-a)$	65.8	°C/W
Thermal resistance, channel to ambient (t = 10 s) (Note 2b)	$R_{th} (ch-a)$	125	°C/W

Marking (Note 4)

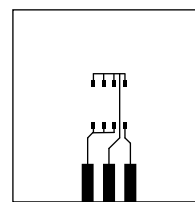


Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: (a) Device mounted on a glass-epoxy board (a) (b) Device mounted on a glass-epoxy board (b)



(a)



(b)

Note 3: $V_{DD} = -24\text{ V}$, $T_{ch} = 25\text{ °C}$ (initial), $L = 500\text{ }\mu\text{H}$, $R_G = 25\text{ }\Omega$, $I_{AR} = -10\text{ A}$

Note 4: • on lower left of the marking indicates Pin 1.

※ Weekly code: (Three digits)



Note 5: A line under a Lot No. identifies the indication of product Labels.

Not underlined: $[[Pb]]/INCLUDES > MCV$

Underlined: $[[G]]/RoHS\ COMPATIBLE$ or $[[G]]/RoHS\ [[Pb]]$

Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product. The RoHS is the Directive 2011/65/EU of the European Parliament and of the Council of 8 June 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.

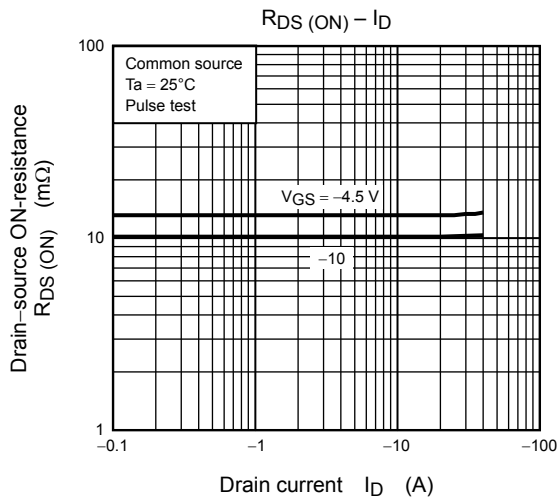
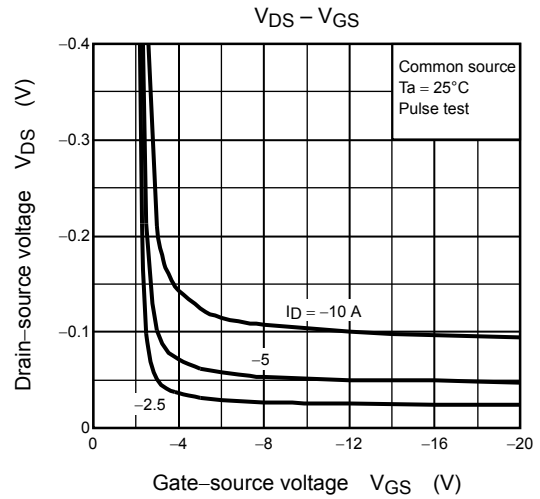
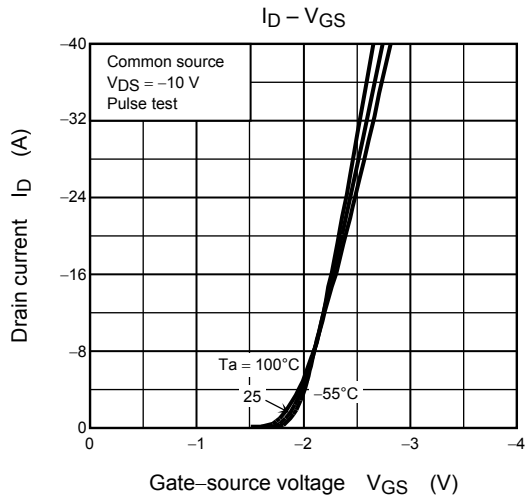
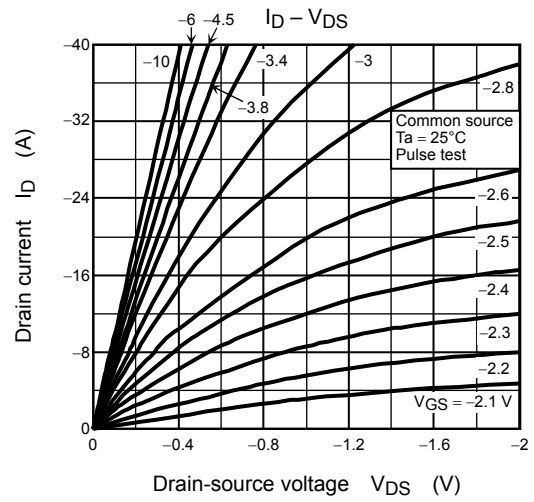
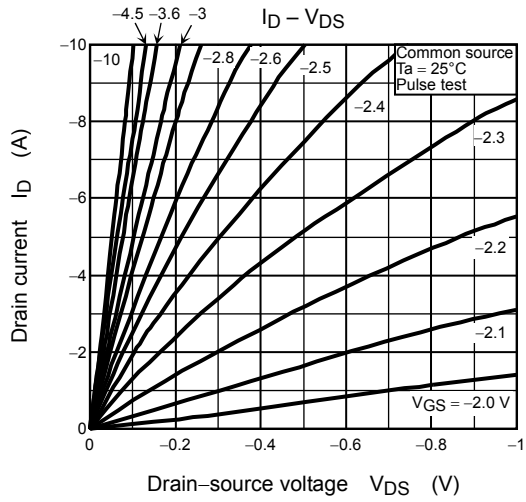
Electrical Characteristics (Ta = 25°C)

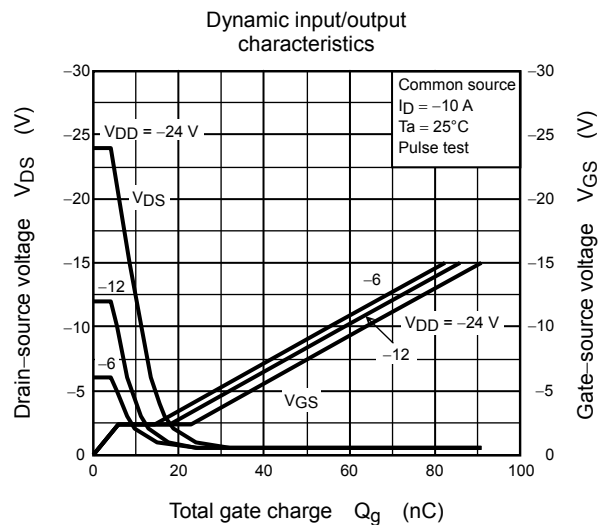
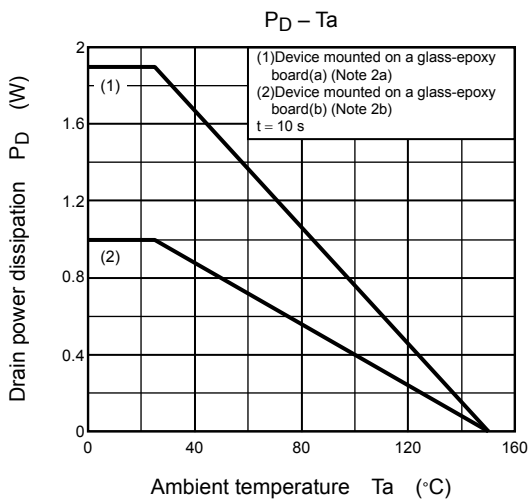
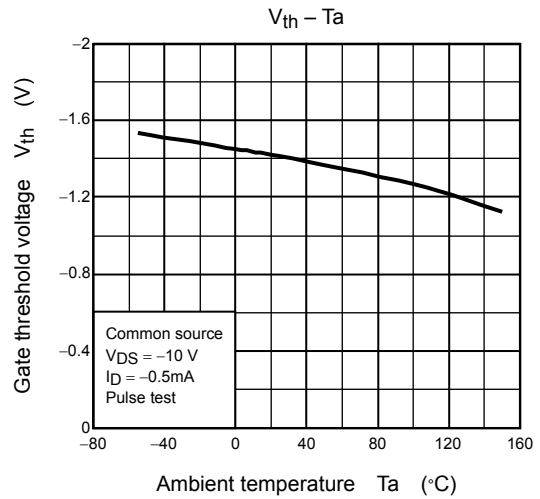
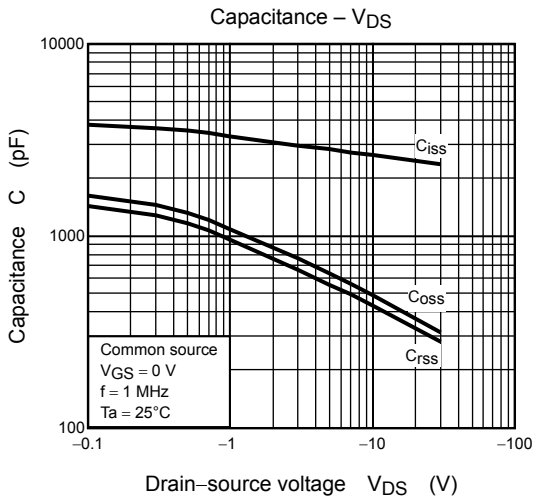
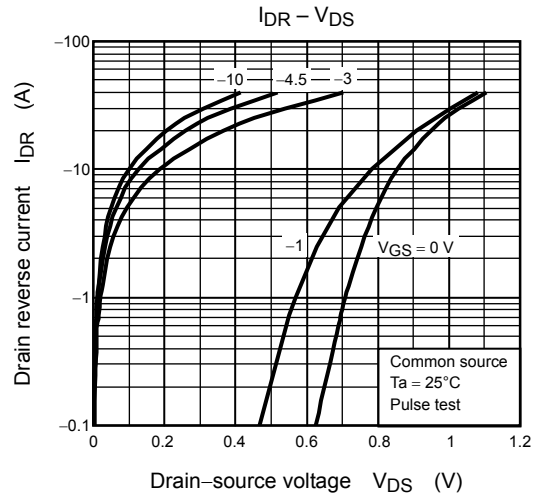
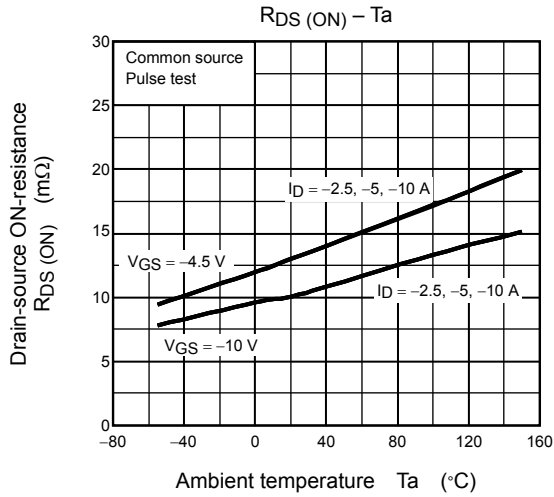
Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		I_{GSS}	$V_{GS} = \pm 20\text{ V}, V_{DS} = 0\text{ V}$	—	—	± 100	nA
Drain cut-OFF current		I_{DSS}	$V_{DS} = -30\text{ V}, V_{GS} = 0\text{ V}$	—	—	-10	μA
Drain-source breakdown voltage		$V_{(BR)DSS}$	$I_D = -10\text{ mA}, V_{GS} = 0\text{ V}$	-30	—	—	V
		$V_{(BR)DSX}$	$I_D = -10\text{ mA}, V_{GS} = 10\text{ V}$ (Note 6)	-21	—	—	
Gate threshold voltage		V_{th}	$V_{DS} = -10\text{ V}, I_D = -0.5\text{ mA}$	-0.8	—	-2.0	V
Drain-source ON-resistance		$R_{DS(ON)}$	$V_{GS} = -4.5\text{ V}, I_D = -5\text{ A}$	—	13	17	m Ω
			$V_{GS} = -10\text{ V}, I_D = -5\text{ A}$	—	10	13	
Input capacitance		C_{iss}	$V_{DS} = -10\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	—	2580	—	pF
Reverse transfer capacitance		C_{rss}		—	430	—	
Output capacitance		C_{oss}		—	490	—	
Switching time	Rise time	t_r		—	8	—	ns
	Turn-ON time	t_{on}		—	16	—	
	Fall time	t_f		—	75	—	
	Turn-OFF time	t_{off}		—	245	—	
Total gate charge (gate-source plus gate-drain)		Q_g	$V_{DD} \approx -24\text{ V}, V_{GS} = -10\text{ V}, I_D = -10\text{ A}$	—	64	—	nC
Gate-source charge 1		Q_{gs1}		—	6	—	
Gate-drain ("miller") charge		Q_{gd}		—	17	—	

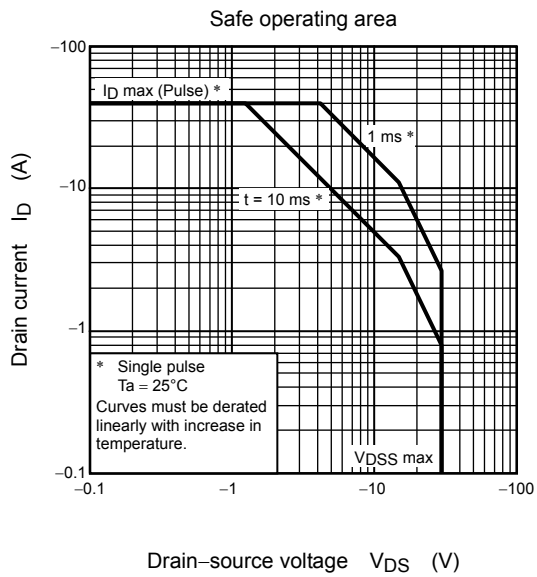
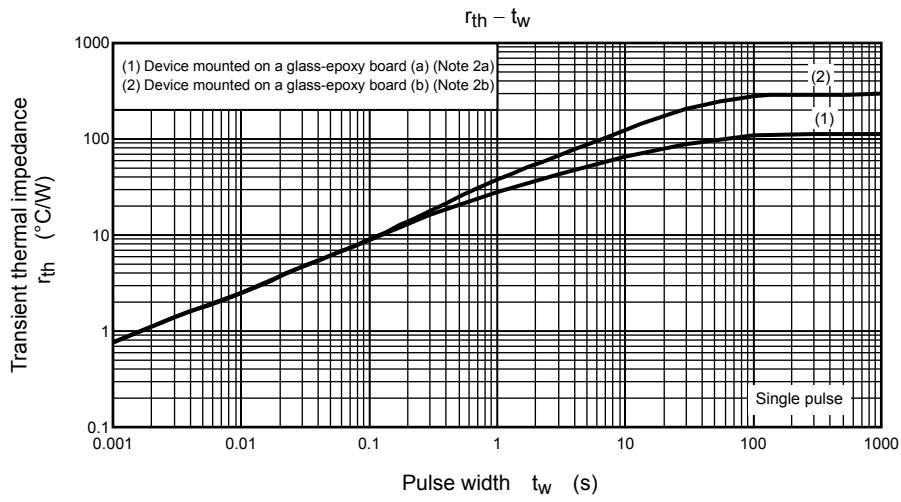
Source-Drain Ratings and Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Drain reverse current	Pulse (Note 1)	I_{DRP}	—	—	—	-40	A
Forward voltage (diode)		V_{DSF}	$I_{DR} = -10\text{ A}, V_{GS} = 0\text{ V}$	—	—	1.2	V

Note 6: VDSX mode (the application of a plus voltage between gate and source) may cause decrease in maximum rating of drain-source voltage.







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